

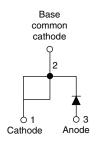
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Vishay Semiconductors

# HEXFRED® Ultrafast Soft Recovery Diode, 8 A



TO-247AC modified



PRODUCT SUMMARY	
Package	TO-247AC modified (2 pins)
I <sub>F(AV)</sub>	8 A
$V_{R}$	600 V
V <sub>F</sub> at I <sub>F</sub>	1.4 V
t <sub>rr</sub> typ.	18 ns
T <sub>J</sub> max.	150 °C
Diode variation	Single die

### **FEATURES**

- Ultrafast and ultrasoft recovery
- Very low I<sub>RRM</sub> and Q<sub>rr</sub>
- Designed and qualified according to JEDEC®-JESD 47







ROHS
COMPLIANT
HALOGEN
FREE
Available

#### **BENEFITS**

- · Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- · Reduced snubbing
- Reduced parts count

#### **DESCRIPTION**

VS-HFA08PB60... is a state of the art center tap ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 8 A continuous current, the VS-HFA08PB60... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I<sub>RRM</sub>) and does not exhibit any tendency to "snap-off" during the to portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA08PB60... is ideally suited applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Cathode to anode voltage	$V_R$		600	V					
Maximum continuous forward current	I <sub>F</sub>	T <sub>C</sub> = 100 °C	8						
Single pulse forward current	I <sub>FSM</sub>		60	А					
Maximum repetitive forward current	I <sub>FRM</sub>		24						
Maximum power dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	36	W					
Maximum power dissipation		T <sub>C</sub> = 100 °C	14	VV					
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +150	°C					



# VS-HFA08PB60PbF, VS-HFA08PB60-N3

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<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Cathode to anode breakdown voltage	V <sub>BR</sub>	I <sub>R</sub> = 100 μA	600	-	-				
Maximum forward voltage		I <sub>F</sub> = 8.0 A		-	1.4	1.7	V		
	$V_{FM}$	I <sub>F</sub> = 16 A	See fig. 1	-	1.7	2.1			
		I <sub>F</sub> = 8.0 A, T <sub>J</sub> = 125 °C		-	1.4	1.7			
Maximum reverse		V <sub>R</sub> = V <sub>R</sub> rated	0	-	0.3	5.0			
leakage current	I <sub>RM</sub>	$T_J = 125$ °C, $V_R = 0.8 \times V_R$ rated	See fig. 2	-	100	500	μA		
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 200 V See fig. 3		-	10	25	pF		
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from p	ackage body	-	8.0	-	nH		

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
	t <sub>rr</sub>	$I_F = 1.0 \text{ A}, dI_F/dt = 200$	A/μs, V <sub>R</sub> = 30 V	-	18	-			
Reverse recovery time See fig. 5, 10	t <sub>rr1</sub>	T <sub>J</sub> = 25 °C	$I_F = 8.0 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	37	55	ns		
000 lig. 0, 10	t <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	55	90			
Peak recovery current	I <sub>RRM1</sub>	T <sub>J</sub> = 25 °C		-	3.5	5.0	A nC		
See fig. 6	I <sub>RRM2</sub>	T <sub>J</sub> = 125 °C		-	4.5	8.0			
Reverse recovery charge	Q <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	65	138			
See fig. 7	Q <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	124	360	110		
Peak rate of fall of recovery current during t <sub>b</sub> See fig. 8	dI <sub>(rec)M</sub> /dt1	T <sub>J</sub> = 25 °C		-	240	-	Λ/μο		
	dI <sub>(rec)M</sub> /dt2	T <sub>J</sub> = 125 °C		-	210	-	- A/μs		

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Lead temperature	T <sub>lead</sub>	0.063" from case (1.6 mm) for 10 s	-	-	300	°C			
Thermal resistance, junction to case	$R_{ heta JC}$		-	-	3.5				
Thermal resistance, junction to ambient	$R_{ heta JA}$	Typical socket mount	-	-	40	K/W			
Thermal resistance, case to heatsink	$R_{\theta CS}$	Mounting surface, flat, smooth and greased	-	0.25	-				
Woight			-	6.0	=	g			
Weight			-	0.21	-	oz.			
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)			
Marking device		Case style TO-247AC modified (JEDEC)		HFA08PB60					

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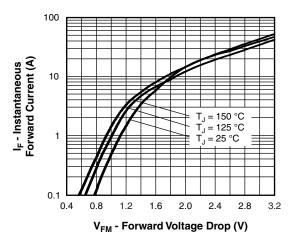


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

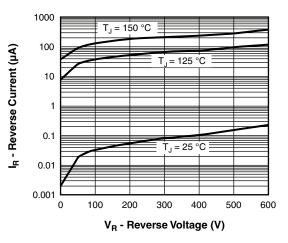


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

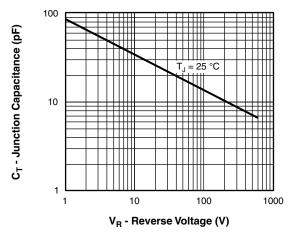


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

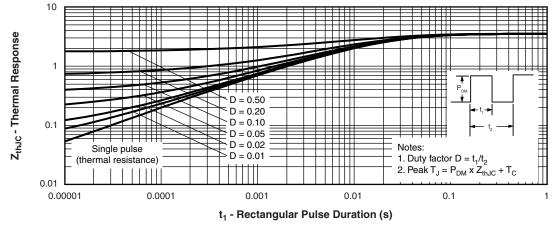


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics



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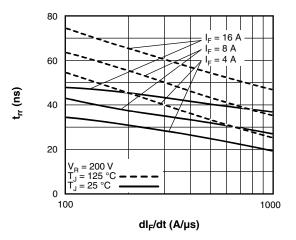


Fig. 5 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt (Per Leg)

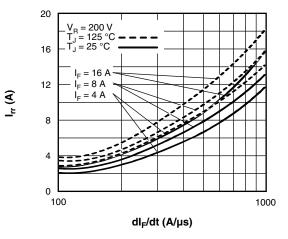


Fig. 6 - Typical Recovery Current vs. dl<sub>F</sub>/dt (Per Leg)

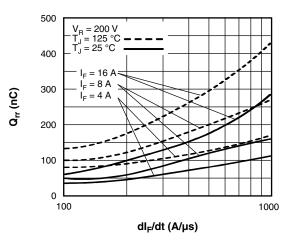


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt (Per Leg)

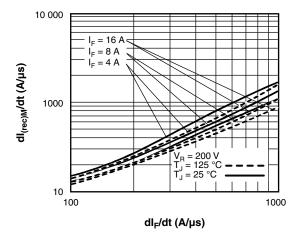


Fig. 8 - Typical dl<sub>(rec)M</sub>/dt vs. dl<sub>F</sub>/dt (Per Leq)

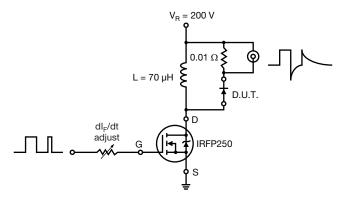
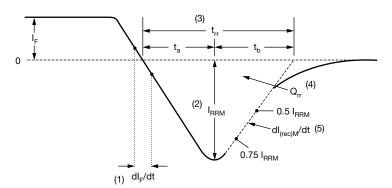


Fig. 9 - Reverse Recovery Parameter Test Circuit

# VS-HFA08PB60PbF, VS-HFA08PB60-N3

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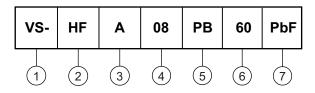


- (1) dl<sub>F</sub>/dt rate of change of current through zero crossing
- (4)  $Q_{rr}$  area under curve defined by  $t_{rr}$  and  $I_{RRM}$
- (2) I<sub>RBM</sub> peak reverse recovery current
- $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$
- (3) t<sub>rr</sub> reverse recovery time measured from zero crossing point of negative going I<sub>F</sub> to point where a line passing through 0.75 I<sub>RRM</sub> and 0.50 I<sub>RRM</sub> extrapolated to zero current.
- (5) dl<sub>(rec)M</sub>/dt peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 10 - Reverse Recovery Waveform and Definitions

### **ORDERING INFORMATION TABLE**

Device code



- Vishay Semiconductors product
- 2 HEXFRED® family
- Electron irradiated
- 4 Current rating (08 = 8A)
- PB = TO-247AC modified
- 6 Voltage rating: (60 = 600 V)
- 7 Environmental digit:

PbF = lead (Pb)-free and RoHS-compliant

-N3 = halogen-free, RoHS-compliant, and totally lead (Pb)-free

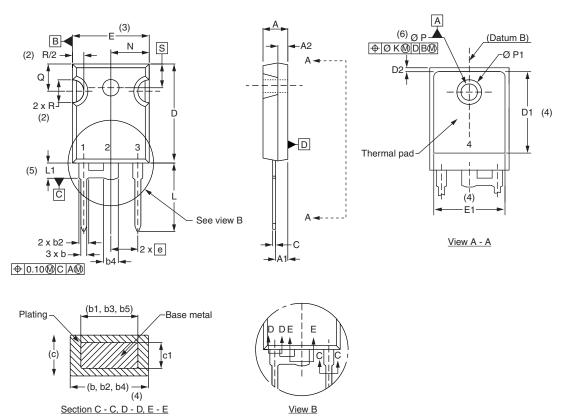
ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-HFA08PB60PbF	25	500	Antistatic plastic tube						
VS-HFA08PB60-N3	25	500	Antistatic plastic tube						

LINKS TO RELATED DOCUMENTS							
Dimensions		www.vishay.com/doc?95541					
Part marking information	TO-247AC modified PbF	www.vishay.com/doc?95255					
	TO-247AC modified -N3	www.vishay.com/doc?95442					

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### TO-247 - 50 mils L/F modified

### **DIMENSIONS** in millimeters and inches



CVMDOL	MILLIN	MILLIMETERS		HES	NOTES	NOTES	CVMDOL	MILLIM	METERS	INC	HES	NOTES
SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.65	5.31	0.183	0.209			D2	0.51	1.35	0.020	0.053	
A1	2.21	2.59	0.087	0.102			E	15.29	15.87	0.602	0.625	3
A2	1.17	1.37	0.046	0.054			E1	13.46	-	0.53	-	
b	0.99	1.40	0.039	0.055			е	5.46	BSC	0.215	BSC	
b1	0.99	1.35	0.039	0.053			ØK	0.2	254	0.0	)10	
b2	1.65	2.39	0.065	0.094			L	14.20	16.10	0.559	0.634	
b3	1.65	2.34	0.065	0.092			L1	3.71	4.29	0.146	0.169	
b4	2.59	3.43	0.102	0.135			N	7.62	BSC	0	.3	
b5	2.59	3.38	0.102	0.133			ØΡ	3.56	3.66	0.14	0.144	
С	0.38	0.89	0.015	0.035			Ø P1	-	7.39	-	0.291	
c1	0.38	0.84	0.015	0.033			Q	5.31	5.69	0.209	0.224	
D	19.71	20.70	0.776	0.815	3		R	4.52	5.49	0.178	0.216	
D1	13.08	-	0.515	-	4		S	5.51	BSC	0.217	'BSC	

#### Notes

- (1) Dimensioning and tolerance per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC® outline TO-247 with exception of dimension c and Q



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Revision: 13-Jun-16 1 Document Number: 91000